

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPN11006PL

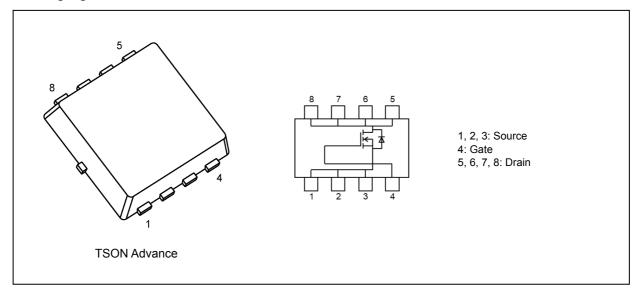
1. Applications

- · High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 5.8 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 14.4 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 8.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 1.5$ to 2.5 V ($V_{DS} = 10$ V, $I_D = 0.2$ mA)

3. Packaging and Internal Circuit



Start of commercial production



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristi	ics		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	60	V
Gate-source voltage	,		V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	26	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)		54	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	119	
Power dissipation	(T _c = 25 °C)		P_{D}	61	W
Power dissipation		(Note 3)		1.6	
Power dissipation		(Note 4)		0.61	
Single-pulse avalanche energy		(Note 5)	E _{AS}	14	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	26	Α
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	2.45	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	93	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	245	

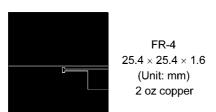
Note 1: Ensure that the channel temperature does not exceed 175 °C.

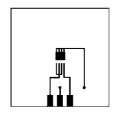
Note 2: Limited 26 A by package capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 48 V, T_{ch} = 25 °C (initial), L = 17 μ H, I_{AS} = 26 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60		_	٧
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	45	_	_	
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.5	_	2.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 5 A	_	12.3	18.1	mΩ
		V _{GS} = 10 V, I _D = 13 A	_	8.8	11.4	

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz	_	1250	1625	pF
Reverse transfer capacitance	C _{rss}		_	25	55	
Output capacitance	C _{oss}		_	225	_	
Gate resistance	r _g	_	_	0.7	1.2	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	2.7	_	ns
Switching time (turn-on time)	t _{on}		_	16	_	
Switching time (fall time)	t _f		_	3.8	_	
Switching time (turn-off time)	t _{off}		_	23	_	

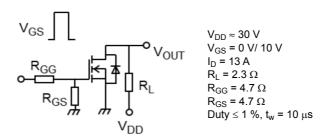


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$	_	17	_	nC
gate-drain)		$V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}$	_	9.0	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$		4.5		
Gate-drain charge	Q_{gd}			3.5		
Gate switch charge	Q_SW			5.8		
Output charge	Q _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	14.4	_	



6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I _{DRP} (t = 100 μs)	_	1	ı	119	Α
Diode forward voltage	V _{DSF}	I _{DR} = 26 A, V _{GS} = 0 V			-1.2	V
Reverse recovery time		V _R = 30 V, I _{DR} = 6.5 A,	_	28	_	ns
Reverse recovery charge	Q _{rr}	$V_{GS} = 0 \text{ V}, -dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$		18	_	nC

Note 7: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

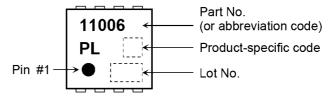


Fig. 7.1 Marking



8. Characteristics Curves (Note)

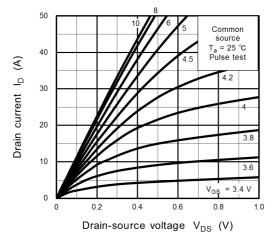
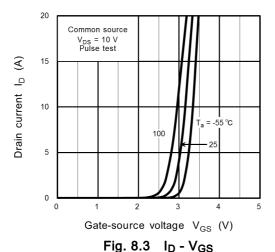


Fig. 8.1 I_D - V_{DS}



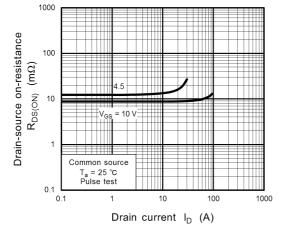


Fig. 8.5 R_{DS(ON)} - I_D

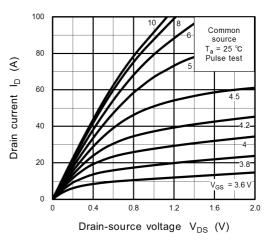


Fig. 8.2 I_D - V_{DS}

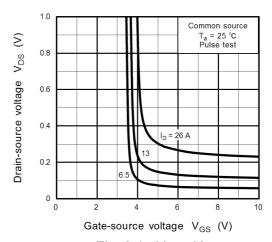


Fig. 8.4 VDS - VGS

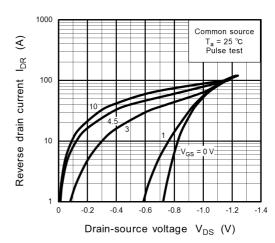


Fig. 8.6 IDR - VDS



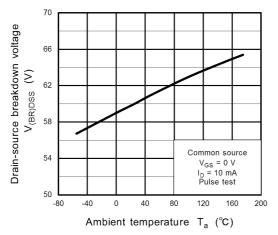


Fig. 8.7 V_{(BR)DSS} - T_a

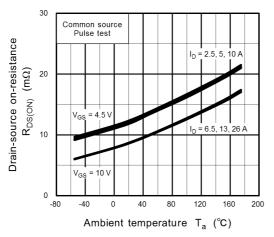


Fig. 8.9 RDS(ON) - Ta

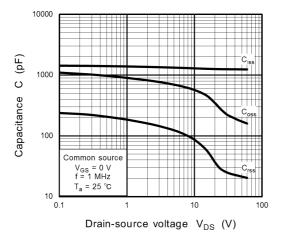


Fig. 8.11 Capacitance - V_{DS}

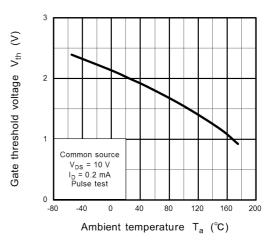


Fig. 8.8 V_{th} - T_a

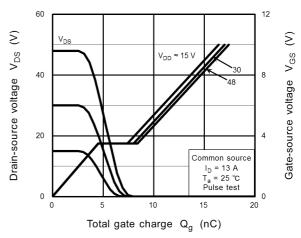


Fig. 8.10 Dynamic Input/Output Characteristics

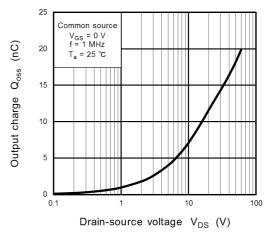


Fig. 8.12 Qoss - VDS



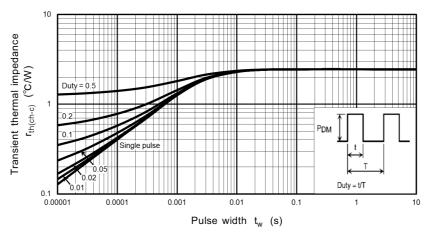


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

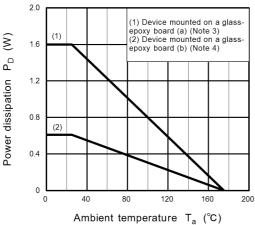


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

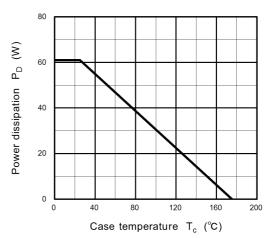


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

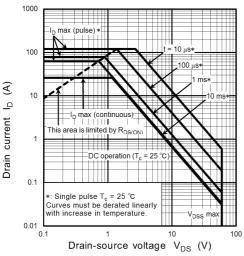


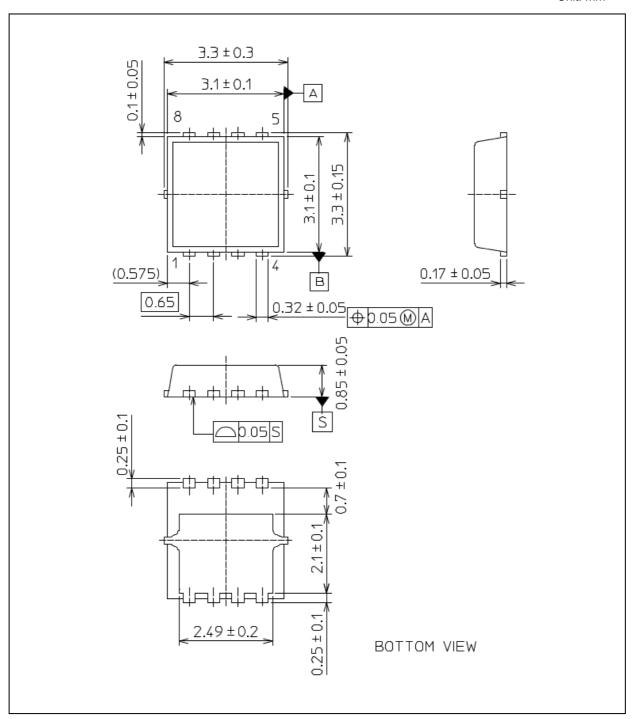
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance



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